

### NCE P-Channel Enhancement Mode Power MOSFET

#### **Description**

The NCE01P18K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications. It is ESD protested.

#### **General Features**

● V<sub>DS</sub> =-100V,I<sub>D</sub> =-18A

 $R_{DS(ON)}\,{<}100m\Omega\;\textcircled{0}\;V_{GS}{=}{-}10V\quad(Typ:85m\Omega)$ 

 $R_{DS(ON)}$  <120m $\Omega$  @  $V_{GS}$ =-10V (Typ:95m $\Omega$ )

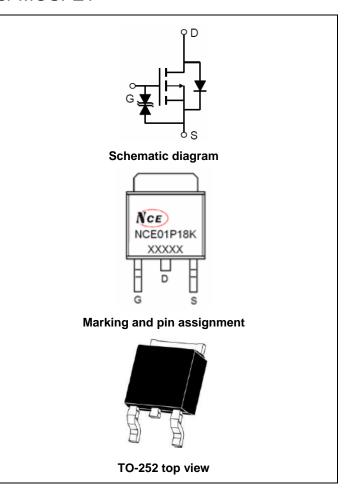
- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low On-Resistance

#### **Application**

- Power management in notebook computer
- Portable equipment and battery powered systems

100% UIS TESTED!

100% AVds TESTED!



### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE01P18K	NCE01P18K	TO-252-2L	-	-	-

### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	-100	V	
Gate-Source Voltage	V <sub>GS</sub>	±20	V	
Drain Current-Continuous	I <sub>D</sub>	-18	А	
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	-12	А	
Pulsed Drain Current	I <sub>DM</sub>	-100	Α	
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	170	mJ	
Maximum Power Dissipation	P <sub>D</sub>	70	W	
Derating factor		0.47	W/℃	
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	$^{\circ}$ C	

#### **Thermal Characteristic**

Thermal Resistance,Junction-to-Case (Note 2)	R <sub>θJc</sub>	2.14	°C/W	
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Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter Symbol		Condition	Min	Тур	Max	Unit				
Off Characteristics	•		•			•				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-100	-	-	V				
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-100V,V <sub>GS</sub> =0V	-	-	1	μA				
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±20	μA				
On Characteristics (Note 3)										
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-1	-1.9	-3	V				
Drain-Source On-State Resistance	В	V <sub>GS</sub> =-10V, I <sub>D</sub> =-16A	-	85	100					
Diain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-16A		95	120	mΩ				
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-50V,I <sub>D</sub> =-10A	5	-	-	S				
Dynamic Characteristics (Note4)										
Input Capacitance	C <sub>lss</sub>	\/ - F0\/\/ -0\/	-	3810	-	PF				
Output Capacitance	Coss	$V_{DS}$ =-50V, $V_{GS}$ =0V, F=1.0MHz	-	129	-	PF				
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVID2	-	125	-	PF				
Switching Characteristics (Note 4)										
Turn-on Delay Time	t <sub>d(on)</sub>		-	16	-	nS				
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =-50V,I <sub>D</sub> =-16A	-	73	-	nS				
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10V, $R_{GEN}$ =9.1 $\Omega$	-	34	-	nS				
Turn-Off Fall Time	t <sub>f</sub>		-	57	-	nS				
Total Gate Charge	$Q_g$	)/ - F0)/I - 40A	-	70	-	nC				
Gate-Source Charge	$Q_{gs}$	$V_{DS}$ =-50V, $I_{D}$ =-16A, $V_{GS}$ =-10V	-	12.5	-	nC				
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =-10V	-	15.5	-	nC				
Drain-Source Diode Characteristics										
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-10A	-	-	-1.2	V				
Diode Forward Current (Note 2)	I <sub>S</sub>	-	-	-	-18	Α				
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF =-16A	-	88.3	-	nS				
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>		65.9	-	nC				
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negli	gible (turr	n-on is do	minated b	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

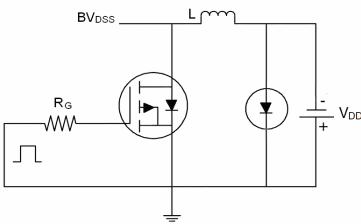
### Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width ≤  $300\mu$ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

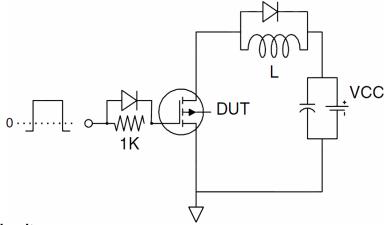


### **Test Circuit**

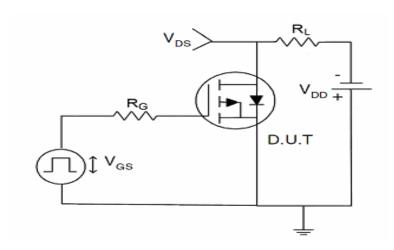
## 1) E<sub>AS</sub> Test Circuit



### 2) Gate Charge Test Circuit

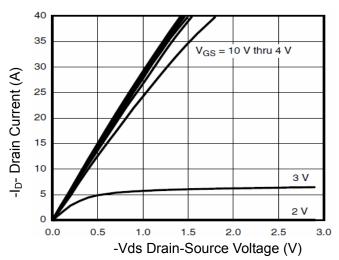


### 3) Switch Time Test Circuit

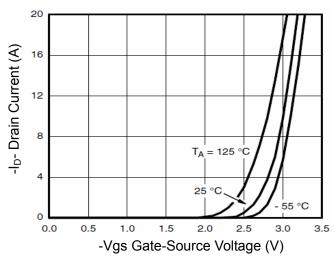




### **Typical Electrical and Thermal Characteristics (Curves)**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

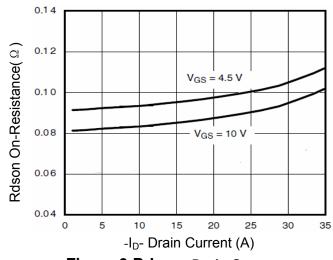


Figure 3 Rdson- Drain Current

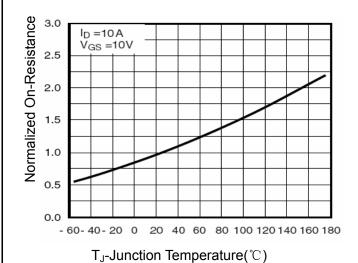


Figure 4 Rdson-JunctionTemperature

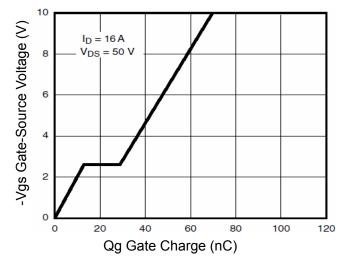


Figure 5 Gate Charge

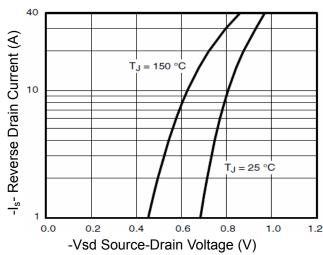
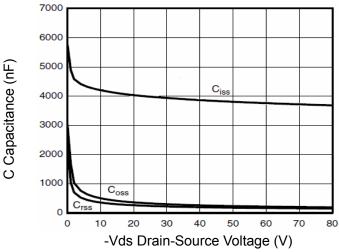


Figure 6 Source- Drain Diode Forward



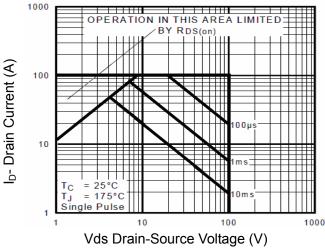


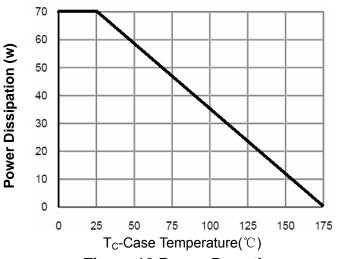
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Figure 7 Capacitance vs Vds

Figure 9 Drain Current vs Case Temperature

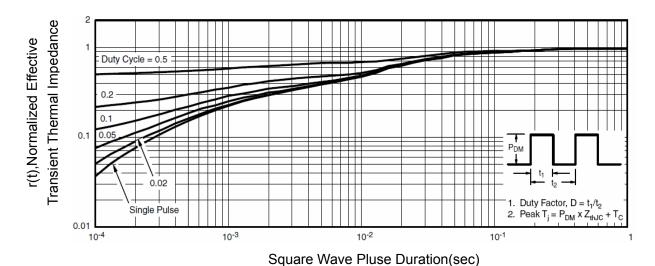
 $T_C$  Case Temperature( $^{\circ}C$ )





**Figure 8 Safe Operation Area** 

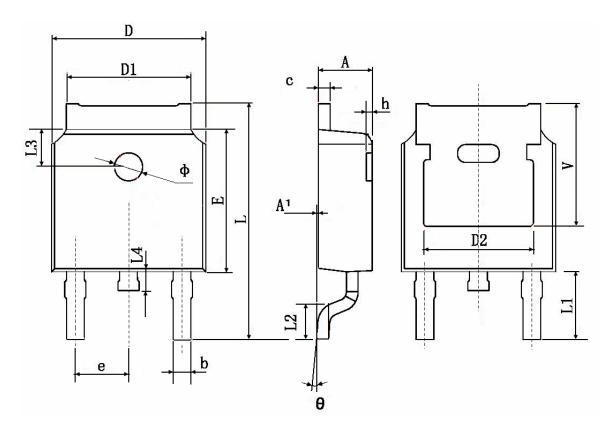
Figure 10 Power De-rating



**Figure 11 Normalized Maximum Transient Thermal Impedance** 



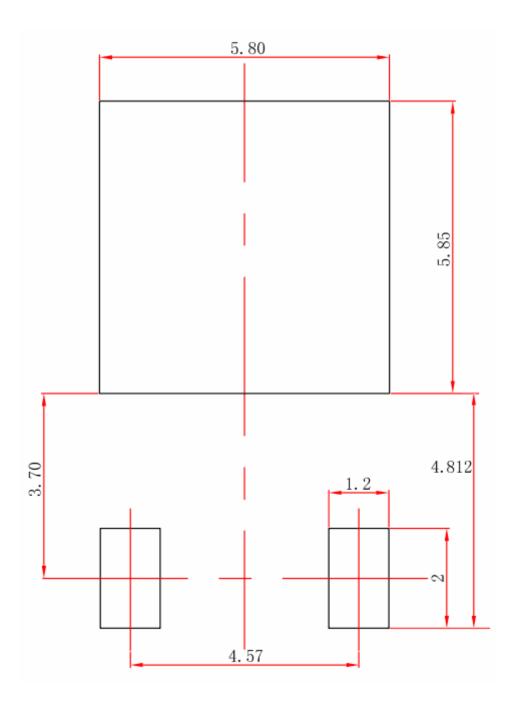
# **TO-252 Package Information**



Comple at	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.8	330 TYP.	0.190	TYP.	
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.90	0 TYP.	0.114	TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.60	0 TYP.	0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.35	0 TYP.	0.21	1 TYP.	



焊盘

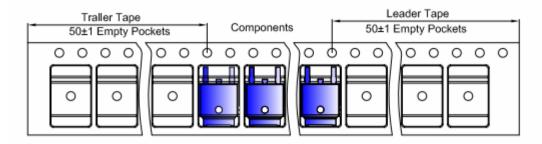


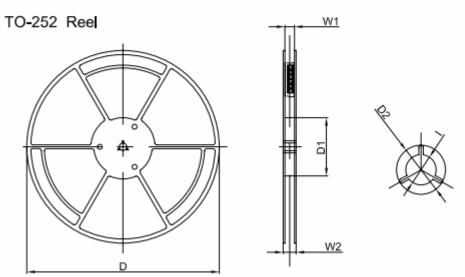
# 技术要求

- 1. 塑封体尺寸6.60×6.10;
- 2. 未注公差为: ±0.05;
- 3. 所有单位为: mm。



## TO-252 Tape Leader and Trailer





Dimensions are in millimeter							
Reel Option	W2	I					
13"Dia	330.00	100.00	Ø21.00	16.40	21.00	Ø13.00	
Tolerance	+/-2	+/-1	+/-1	+/-1	+/-1	+/-1	

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13inch	2,500 pcs	340×336×29	25,000 pcs	353×346×365	14.04



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